High Voltage NPN Silicon Power Transistors

 \dots designed for line operated audio output amplifier, Switchmode power supply drivers and other switching applications.

- 250 V to 400 V (Min) VCEO(sus)
- 1 A Rated Collector Current
- Popular TO-220 Plastic Package

MAXIMUM RATINGS

Rating	Symbol	TIP47	TIP48	TIP49	TIP50	Unit
Collector–Emitter Voltage	VCEO	250	300	350	400	Vdc
Collector-Base Voltage	VCB	350	400	450	500	Vdc
Emitter-Base Voltage	VEB	5.0				Vdc
Collector Current — Continuous Peak	IC	1.0 2.0			Adc	
Base Current	ΙΒ	0.6			Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32			Watts W/°C	
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016			Watts W/°C	
Unclamped Inducting Load Energy (See Figure 8)	Е	20			mJ	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150			°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	3.125	°C/W
Thermal Resistance, Junction to Ambient	RAJA	62.5	°C/W

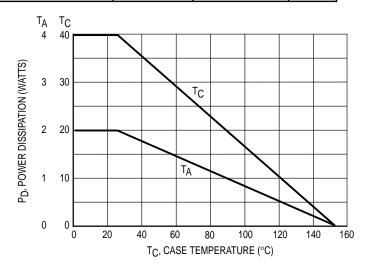


Figure 1. Power Derating

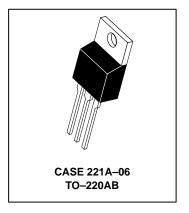
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

TIP47* TIP49* TIP48* TIP50*

*Motorola Preferred Device

1.0 AMPERE
POWER TRANSISTORS
NPN SILICON
250-300-350-400 VOLTS
40 WATTS



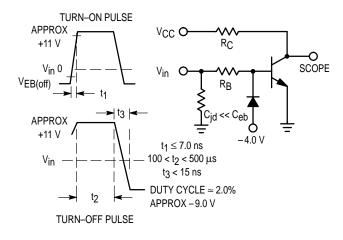


TIP47 TIP49 TIP48 TIP50

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	•
Collector–Emitter Sustaining Voltage (1) (I _C = 30 mAdc, I _B = 0)	TIP47 TIP48 TIP49 TIP50	VCEO(sus)	250 300 350 400	_ _ _ _	Vdc
Collector Cutoff Current (VCE = 150 Vdc, IB = 0) (VCE = 200 Vdc, IB = 0) (VCE = 250 Vdc, IB = 0) (VCE = 300 Vdc, IB = 0)	TIP47 TIP48 TIP49 TIP50	ICEO	_ _ _ _	1.0 1.0 1.0 1.0	mAdc
Collector Cutoff Current (VCE = 350 Vdc, VBE = 0) (VCE = 400 Vdc, VBE = 0) (VCE = 450 Vdc, VBE = 0) (VCE = 500 Vdc, VBE = 0)	TIP47 TIP48 TIP49 TIP50	ICES	_ _ _ _	1.0 1.0 1.0 1.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		IEBO	_	1.0	mAdc
ON CHARACTERISTICS (1)				•	
DC Current Gain (I _C = 0.3 Adc, V _{CE} = 10 Vdc) (I _C = 1.0 Adc, V _{CE} = 10 Vdc)		hFE	30 10	150 —	_
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.2 Adc)		V _{CE(sat)}	_	1.0	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)		V _{BE(on)}	_	1.5	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 0.1 Adc, V _{CE} = 10 Vdc, f = 2.0 MHz)	_	fΤ	10	_	MHz
Small–Signal Current Gain (IC = 0.2 Adc, VCE = 10 Vdc, f = 1.0 kHz)		h _{fe}	25	_	_

⁽¹⁾ Pulse Test: Pulse width $\leq 300 \, \mu s$, Duty Cycle $\leq 2.0\%$.





1.0 0.5 0.2 0.02 0.01 0.02 0.02 0.03 0.04 0.05 0.02 0.05 0.002 0.01 0.02 0.05 0.05 0.002 0.01 0.02 0.05 0.05 0.05 0.06 0.07 0.08 0.09 0

Figure 3. Turn-On Time

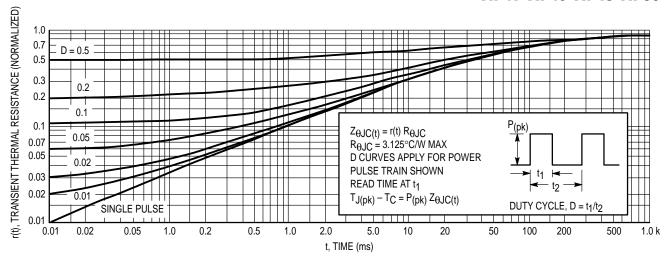


Figure 4. Thermal Response

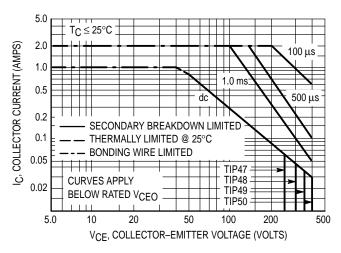


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

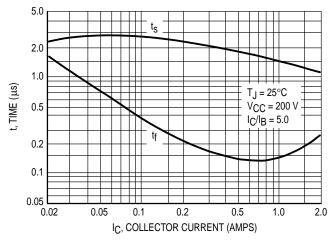


Figure 6. Turn-Off Time

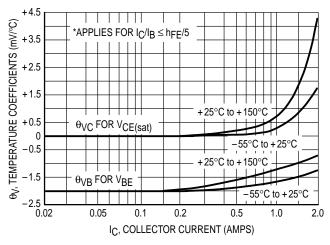


Figure 7. Temperature Coefficients

TIP47 TIP49 TIP48 TIP50

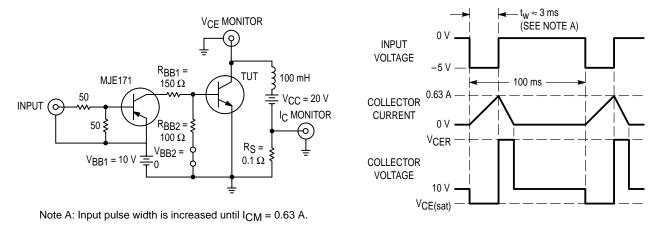


Figure 8. Inductive Load Switching

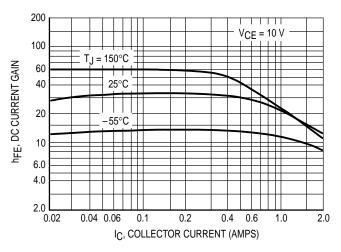


Figure 9. DC Current Gain

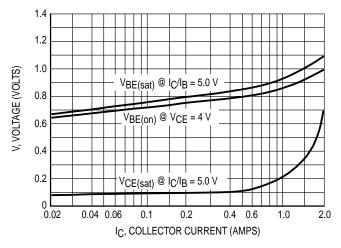
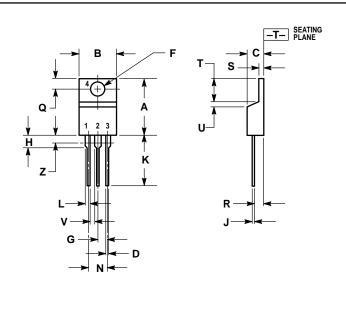


Figure 10. "On" Voltages

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
J	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**

TIP47 TIP49 TIP48 TIP50

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